Cd-doping effects in Ce_2MIn_8 (M = Rh and Ir) heavy fermion compounds

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Low temperature magnetic properties of Cd-doped Ce₂MIn₈ (M = Rh and Ir) single crystals are investigated. Experiments of temperature dependent magnetic susceptibility, heat capacity and electrical resistivity measurements revealed that Cd-doping enhances the antiferromagnetic (AFM) ordering temperature from $T_N = 2.8$ K (x = 0) to $T_N = 4.8$ K (x = 0.21) for Ce₂RhIn_{8-x}Cd_x and induces long range AFM ordering with $T_N = 3.8$ K (x = 0.21) for Ce₂IrIn_{8-x}Cd_x. Additionally, X-ray and neutron magnetic scattering studies showed that Cd-doped samples present below T_N a commensurate antiferromagnetic structure with a propagation vector $\vec{\varepsilon} = (\frac{1}{2}, \frac{1}{2}, 0)$. The resolved magnetic structures for both compounds indicate that the Cd-doping tends to rotate the direction of the ordered magnetic moments toward the ab-plane. This result suggests that the Cd-doping affects the Ce³⁺ ground state single ion anisotropy modifying the crystalline electrical field (CEF) parameters at the Ce³⁺ site. Indications of CEF evolution induced by Cd-doping were also found in the electrical resistivity measurements. Comparisons between our results and the general effects of Cd-doping on the related compounds CeMIn₅ (M = Co, Rh and Ir) confirms the claims that the Cd-doping induced electronic tuning is the main effect favoring AFM ordering in these compounds.

I. INTRODUCTION

 Ce_2MIn_8 (M = Rh, Ir) are heavy-fermions compounds that belong to the broader family Ce_nMIn_{3n+2} (M = Co, Rh, Ir; n=1, 2) where the occurrence of unconventional superconductivity (USC) in various members has provided a great opportunity to further study the relationship between magnetism, USC and crystal structure. For the heavy-fermion superconductors (HFS) in this family, USC is believed to be mediated by magnetic fluctuations^{1,2} and their critical temperatures seem to be related to the dimensionality of their crystal structures.^{3,4,5,6,7} In fact, they are tetragonal variants of the cubic CeIn₃ structure with a layer of MIn₂ introduced between n-blocks of CeIn₃ along the c-axis.^{3,4}

Particularly interesting in these series is the tunability of their ground state (GS) by pressure and/or doping which leads to remarkable phase diagrams showing interplay between USC and antiferromagnetism (AFM) and the presence of quantum critical phenomena. 2,3,4,5,6,7,8,9,10,11,12,13,14,15,16,17,18,19 For instance, applied pressure induces a high pressure superconducting phase in the ambient pressure AFM members of this family, n = 1 (115) member CeRhIn₅ ($T_N = 3.8$ K) and n = 2 (218) member Ce₂RhIn₈ ($T_N = 2.8 \text{ K}$).^{2,3,9,10} The under pressure properties of the single layer member CeRhIn₅ were much more extensively studied. Not long ago, evidence for hidden AFM order inside the SC state has been found in CeRhIn₅ under pressure and magnetic field.² The importance of simultaneous spin and charge fluctuations associated with a QCP for the superconductivity in this material has been shown.⁹

Regarding the doping phase diagrams of the

 Ce_nMIn_{3n+2} (M =Co, Rh, Ir; n = 1, 2) compounds, again the 115 members have been the main focus of the reported studies in the literature. For example, the reports on the $CeRh_{1-x}(Co, Ir)_xIn_5$ phase diagrams ^{5,7,8} reveal coexistence between AFM and SC for a large range of x. Furthermore the critical temperatures of the superconducting samples varies linearly with the c/a ratio of the lattice parameters of the compounds¹¹. Many other chemical substitutions were made in the 115 materials to contribute to the understanding of the microscopic tuning parameter of their GS.^{11,12,13,14,15,16,17,18,19} Ladoping on the Ce³⁺ site for AFM members of the family Ce_nMIn_{3n+2} (M = Co, Rh, Ir; n = 1, 2) were aimed to describe the suppression the of the Néel temperature by dilution and the effect of dimensionality on the percolation AFM ordering.¹⁹

Indeed more revealing doping studies were made by the substitution of In by $\operatorname{Sn}^{12,13,14,15}$ and $\operatorname{Cd}^{16,17,18}$. This is because In, Cd and Sn are not isovalent. While Sn has one more p-electron than In, Cd has one p-electron less, and thus opposite electronic effects might be expected. However, it was found that both elements suppress the SC state in $CeMIn_5$ for M = Co and Ir, while Cd-substitution tends to favor AFM ordering but Sndoping leads to its suppression. 13,14,15,16,17,18 The microscopic mechanisms of this doping that tune the GS in the CeMIn₅ compounds were attributed to the electronic tuning. It is therefore important and elucidative to explore the behavior for the other series in the Ce_nMIn_{3n+2} (M = Co, Rh, Ir; n = 1, 2) family and determine to what extent the same interpretation holds. In this regard, to study the n=2 member of the Ce_nMIn_{3n+2} family, the Ce₂MIn₈ could be particulary interesting since Cd and

Sn doping are also possible in the 218's and they present an intermediate step in terms of dimensionality between the cubic CeIn3 and the 115 compounds.^{20,21}

Recently, interest in the 218 family has increased due to the discovery of the first HFS with a transition metal different from Co, Rh or Ir, in the HF $\mathrm{Ce}_m\mathrm{MIn}_{3m+2}$ family. $\mathrm{Ce}_2\mathrm{PdIn}_8$ was found to be an antiferromagnet ($T_N=10~\mathrm{K}$) and an ambient pressure SC ($T_c\sim0.68~\mathrm{K}$). It has not yet been established whether SC in this compound has an unconventional character or if it coexists with the magnetism on a microscopic scale²².

To further explore the microscopic effects for Cd-doping in the $\mathrm{Ce_nMIn_{3n+2}}$ (M = Co, Rh, Ir; n=1, 2) family we present in this article the evolution of the low temperature physical properties of the $\mathrm{Ce_2MIn_8}$ (M = Rh, Ir) as a function of the Cd-substitution. It is reported how the $T_N=2.8$ K and the magnetic structure (with $\vec{\varepsilon}=(\frac{1}{2},\frac{1}{2},0))^{23}$ of $\mathrm{Ce_2RhIn_8}$ evolves as a function of Cd-doping. Also the effects of Cd-doping on the low temperature spin glass phase $(T_g=0.6~\mathrm{K})^{24}$ of the HF $\mathrm{Ce_2IrIn_8}$ are investigated. Our results are compared to those found for the Ce115's compounds and a discussion of the microscopic effect of the Cd in the GS of these systems are also given.

II. EXPERIMENTAL DETAILS

Single crystalline samples of Ce_2MIn_8 (M = Rh, Ir) doped with Cd were grown from Indium flux in which various amounts of Cd were added to the flux, 25,26 so that the nominal concentration of Cd can be defined by the Cd/In ratio used in the growth. We have performed prompt gamma neutron activation measurements on the instrument NG7 of the NIST Center for Neutron Research of the National Institute of Standards and Technology which reveal that the real Cd concentration in a given crystal is about 13 % of the nominal concentration for samples of both series studied in this work. A detailed analysis of the actual Cd concentration in Cddoped CeMIn₅ made by Pham et al¹⁶ showed that the Cd concentration in these crystals is approximately 10 % of that in the flux from which they were grown. In this work it will be used and labelled in the figures the real Cd concentration measured by prompt gamma neutron activation.

The tetragonal (P4/mmm) structure and unit cell parameters of all samples were determined by X-ray powder diffraction. Within the range of Cd-concentrations studied no appreciable changes in the lattice parameters due the Cd-doping were observed. Magnetization measurements as a function of the temperature were performed using a commercial superconducting quantum interference device (SQUID) in the temperature range between 2.0 and 300 K. Specific heat and electrical resistivity experiments were performed in a commercial physical properties measurement system (PPMS) in the temperature range between 0.3 and 10 K for the specific heat measure-

ments and between 1.9 and 300 K for the resistivity ones. The specific heat set up uses a small mass calorimeter that employs a quasi-adiabatic thermal relaxation technique, while the electrical resistivity was measured using a low-frequency ac resistance bridge and four-contact configuration. The samples were screened and previously found to be free of surface contamination by residual Influx

For the X-ray magnetic scattering (XMRS) experiments, a selected crystal of Cd-doped Ce₂RhIn₈ with x = 0.21 was prepared with polished (00l) flat surface, and approximately 3 mm x 2 mm x 1 mm. The mosaic spread of the sample was found to be $< 0.05^{\circ}$ by a rocking curve (θ scan) on a four circle diffractometer. XRMS studies were performed at the ID-20 beamline at the European Synchrotron Radiation Facility (ESRF). The ID-20 X-ray source is a linear undulator with a 32 mm period. The main optical components are a double Si(111) crystal monochromator with sagittal focusing and two meridional focusing mirrors on either side of the monochromator. The sample was mounted on a cryostat (with a base temperature of 1.7 K using a Joule-Thomson stage), installed on a four-circle diffractometer with the a-axis parallel to the beam direction. This configuration allowed σ -polarized incident photons in the sample. In a second run, the sample was mounted in a horizontal four circle diffractometer with the (110) direction parallel to the beam direction and this configuration allowed π -polarized incident photons in the samples. During all measurements we performed a polarization analysis, using LiF(220) crystal analyzer, appropriate for the energy of Ce-L₂ absorption edge.

For the neutron magnetic scattering (NMS) experiments, selected crystals of Cd doped Ce_2RhIn_8 and Ce_2IrIn_8 both with x=0.21 of Cd were prepared with sizes of approximately 4 mm x 3 mm x 1 mm. NMS measurements were carried out on BT-9 triple axis neutron spectrometer of the NIST Center for Neutron Research (NCNR). The samples were cooled in an ILL orange cryostat (with a base temperature of 1.7 K), the horizontal collimators used were 40-47-40-80. Neutrons with incident energy $E=35~{\rm meV}$ were selected using the (002) reflection of a pyrolytic graphite monocromator, and filter to suppress the higher harmonics. Uncertainties where indicated are statistical in nature and represent one standard deviation.

III. RESULTS AND DISCUSSIONS

A. Macroscopic properties of $Ce_2(Rh,Ir)In_{8-x}Cd_x$

Figure 1 shows the temperature dependence in the low-T region of the magnetic susceptibility measured for a magnetic field H = 0.1 T applied parallel $\chi_{//}$ (closed symbols), and perpendicular χ_{\perp} (open symbols) to the c-axis for pure and Cd-doped (a) Ce₂RhIn₈ and (b) Ce₂IrIn₈ single crystals with Cd concentrations of 0.03 (triangles)

and 0.21 (squares). The inset in each panel shows the magnetic susceptibility as a function of the temperature from 2.0 K to 300 K for the samples with x = 0.21. The results in Fig. 1a for Cd-doped Ce₂RhIn₈ show AFM order for $T_N \approx 5.0$ K for x = 0.21 of Cd and $T_N \approx 4.0$ K for x = 0.03 of Cd. The results in Fig. 1b for Cddoped Ce₂IrIn₈ show AFM order at $T_N \approx 3.8$ K for x =0.21 and no magnetic order to 2.0 K for x = 0.03. For both materials the magnetic susceptibility is larger for a field applied along the c-axis, in agreement to what was found for the compounds in the In-based $R_m M_n In_{3m+2n}$ (M = Co, Rh or Ir, M = 1, 2) series (except for R =Gd).^{27,28,29,30,31} For the whole series the susceptibility is anisotropic and the ratio $\chi_{//}/\chi_{\perp}$ taken at T_N is mainly determined by the tetragonal crystalline electrical field (CEF) and reflects to some extent the CEF anisotropy. The ratio remains nearly constant as a function of Cddoping for each family, for example, for M = Rh the values of the ratio are roughly 1.6 and 1.5 for the samples with x = 0.21 and 0.03, respectively. For M = Ir the value of the ratio is nearly 2.2 and 2.1 for samples with x = 0.21 and 0.03, respectively. Fits from the polycrystalline average of the magnetic susceptibility data taken as $\chi_{poly} = (\chi_{//} + 2\chi_{\perp})/3$ for T > 150 K using a Curie-Weiss law yield an effective magnetic moment μ_{eff} = $2.48(8) \mu_B$ and a paramagnetic Curie-Weiss temperature $\theta_p = -44(1) \text{ K for M} = \text{Rh}, x = 0.21, \text{ and } \mu_{eff} = 2.51(6)$ μ_B and $\theta_p = -42(1)$ K for M = Ir. The values of μ_{eff} and θ_p do not change significantly as a function of the Cd-concentration for both series in the range of concentration studied.

Figure 2 shows the Cd-doping induced evolution of the low temperature magnetic specific-heat C_{mag} divided by temperature for (a) $Ce_2RhIn_{8-x}Cd_x$ and (b) $Ce_2IrIn_{8-x}Cd_x$ single crystals. To obtain the magnetic specific-heat the lattice specific-heat contribution (C_{latt}) was estimated from the specific-heat data of La₂RhIn₈ (not shown) and subtracted from the total specific heat (C_T) of each compound. The results of the specific-heat measurements for both series clearly show an enhancement of the AFM order as a function of Cd content in both systems. It is interesting to note that even for the samples with larger quantity of Cd, the phase transition anomaly is still a sharp and well defined peak, indicating a good quality of the crystals and a reasonably homogenous distribution of Cd concentration in the samples. More interesting is the case of $Ce_2IrIn_{8-x}Cd_x$ in which the spin glass phase of the pure compound seems to evolve to a long range AFM with increasing doping even though doping typically tends to increase disorder. This result suggests that the presence of a stronger Kondo effect in Ce₂IrIn₈ is relevant to the formation of the frustrated spin system in this compound.

The insets of both panels of Fig. 2 show the corresponding magnetic entropy per mole Ce for the pure and Cd-doped compounds in units of Rln2. For $\text{Ce}_2\text{RhIn}_{8-x}\text{Cd}_x$ the recovered magnetic entropy for x=0.21 at 10 K is about 0.75 Rln2 (closed diamonds) that

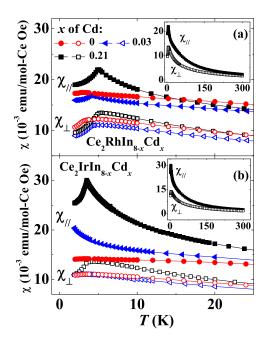


FIG. 1: Temperature dependence of the magnetic susceptibility in the low-T region for Cd-doped (a) Ce₂RhIn₈ and (b) Ce₂IrIn₈ single crystals (pure compounds (circles), x=0.03 (triangles) and x=0.21 (squares)). The magnetic field H = 0.1 T was applied parallel $\chi_{//}$ (closed symbols), and perpendicular χ_{\perp} (open symbols) to the c-axis. The insets in both panels show the magnetic susceptibility as a function of the temperature from 2.0 K to 300 K for x=0.21 of Cd in both systems. 1 emu/(mol Oe) = $4 \pi 10^-6$ m³/mol.

is a value larger than the recovered magnetic entropy seen for the pure compound (0.65 Rln2, closed circles) at the same temperature. In the case of $\mathrm{Ce_2IrIn_{8-x}Cd_x}$ the entropy of the Cd-doped sample is just slightly larger than the entropy of the pure compound. These results suggest the magnetic entropy is increasing as a function of the Cd concentration. On the other hand, the recovered magnetic entropies for these compounds still do not recover the Rln2 value expected for the entropy of the ground state doublet, suggesting the presence of partly compensated Kondo ordered moments.

Figure 3 summarizes the temperature-doping phase diagrams resulting from heat capacity measurements for $\text{Ce}_2 \text{MIn}_{8-x} \text{Cd}_x$ (closed symbols), together with the results found by Pham $et~al.^{16}$ for CeMIn_5 (open symbols) for M=Rh (squares) and Ir (circles). For $\text{Ce}_2 \text{RhIn}_{8-x} \text{Cd}_x$ one can observe the evolution of the Néel temperature from 2.8 K for the pure compound to 4.8 K to x=0.21 of Cd. For higher Cd-concentrations T_N remains constant up x=0.35. In this range of concentration there seems to be a saturation of the Cd incorporation into the compound. For $\text{Ce}_2 \text{IrIn}_{8-x} \text{Cd}_x$ one can observe that a very small Cd concentrations (x=0.03)

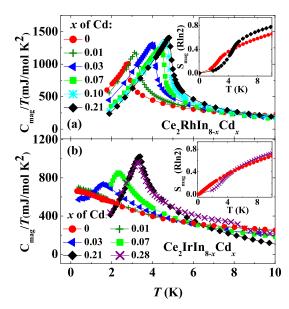


FIG. 2: Magnetic specific-heat data ($C_{mag} = C_T - C_{latt}$) divided by temperature as a function of temperature for (a) $Ce_2RhIn_{8-x}Cd_x$ and (b) $Ce_2RhIn_{8-x}Cd_x$ single crystals for various Cd concentrations. The insets in each panels show the magnetic entropy S_{mag} for both systems.

favors the establishment of long range AFM order when the undoped²⁴ compound is a spin glass. The maximum value of T_N for M = Ir is 3.8 K for x=0.21 of Cd. For higher x again a saturation of the Cd incorporation in samples is observed.

Therefore the results of figure 3 reveal that Cd-doping favors AFM ordering in both $CeMIn_5$, (M = Co, Rh, $Ir)^{16}$ and Ce_2MIn_8 (M = Rh, Ir) HF families. To further compare our results with those found by Pham et al. 16 for Cd-doped Ce115, we notice that, for CeRhIn₅, the Cd-doping first reduces the T_N from 3.8 K for undoped material to 3.0 K, with a flat minimum for Cd concentration between 0.05 and 0.10. Higher Cd concentrations lead to a Néel temperature increase up to 4.2 K for $x \sim$ 0.15. This behavior in Cd-doped CeRhIn₅ was suggested to be connected with an incommensurate to commensurate magnetic ordering evolution that can be induced by Cd-doping in CeRhIn₅¹⁶. In Cd-doped Ce₂RhIn₈ we found that T_N is always increasing with the Cd concentration. The fact that pure Ce₂RhIn₈ already shows just below $T_N=2.8$ K a commensurate magnetic structure (with $\vec{\varepsilon}=(\frac{1}{2},\frac{1}{2},0))^{23}$ may explain the difference between the two structures.

For CeIrIn₅ the Cd-doping initially suppress the superconductor state and for concentrations larger than 0.08 the AFM state appear and the increase of Cd content results in an increase of T_N from 2.0 K to around 8.0 K for x=0.15. In the case of Cd-doped Ce₂IrIn₈ we found that the spin glass state of the pure compound evolves to a long range AFM state and T_N also increases as a function of x, but the maximum $T_N \sim 3.8$ K achieved is smaller than the one found for Cd-doped CeIrIn₅. ¹⁶

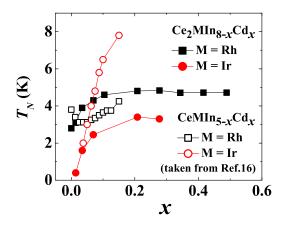


FIG. 3: T_N as a function of Cd concentration for $\text{Ce}_2\text{MIn}_{8-x}\text{Cd}_x$ (closed symbols) and $\text{CeMIn}_{5-x}\text{Cd}_x$ (open symbols) for M = Rh (squares) and Ir (circles). The 115's results were taken from Ref.16 for comparison.

The favoring of AFM in the Cd-doped 115's was interpreted using a Doniach-like scenario³² where the Cd is inducing a decrease of the local density of states at the Ce³⁺ site which tends to reduce the Kondo effect favoring the AFM ordering¹⁶. The behavior of T_N found here for the Cd-doped 218 compounds corroborates this interpretation since the same Cd-doping effect would be expected to happen.

The temperature dependence in the low-T region of the electrical resistivity $\rho(T)$ is plotted in Figure 4 panel (a) for M = Rh and Cd concentrations of x = 0.03 (triangles) and 0.21 (diamonds), and panel (b) for M = Irand Cd concentrations of 0.07 (squares) and 0.21 (diamonds). The insets in Fig. 4 (a) and (b) show the behavior of the electrical resistivity for the entire range of temperatures for the samples with x = 0.21 of Cd for both systems. For all crystals of the two series, the roomtemperature value of the electrical resistivity ranges between 40-80 $\mu\Omega$ cm. Their high-temperature data show a weak metallic behavior down to 150 K, then the resistivity increases reaching a well-defined maximum at a temperature T_{MAX} , around 5.0-10 K (insets of the panels (a) and (b)). The value of T_{MAX} from the resistivity measurements for all compounds as a function of the Cd content is plotted in Fig. 4c for $Ce_2RhIn_{8-x}Cd_x$ (open triangles) and $Ce_2IrIn_{8-x}Cd_x$ (closed triangles).

The results of the resistivity at low-T in Fig. 4a for $\text{Ce}_2\text{RhIn}_{8-x}\text{Cd}_x$ are showing clear kinks around 2.8 K, 3.8 K and 4.8 K for x=0, 0.03 and 0.21 respectively, in good agreement with the values obtained for specificheat measurements for the same values of x. Also for Cd-doped Ce_2IrIn_8 in Fig. 4b one can observe the kink in the resistivity measurements for x=0.21. The other curves for pure and Cd-doped Ce_2IrIn_8 with x=0.07 do not show obvious kinks at T_N , perhaps because the AFM ordering has not yet become long range for these Cd-concentrations. The residual resistivity of the single crystals of Cd-doped Ce_2MIn_8 (M = Rh, Ir) is roughly

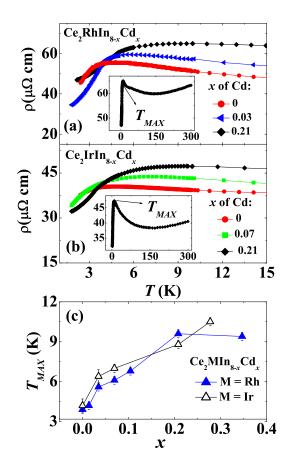


FIG. 4: Temperature dependence of the electrical resistivity $\rho(T)$ in the low-T region for: (a) $\text{Ce}_2\text{RhIn}_{8-x}\text{Cd}_x$ and (b) $\text{Ce}_2\text{IrIn}_{8-x}\text{Cd}_x$ compounds. The insets in each panels show $\rho(T)$ from 2.0 K to 300 K for x=0.21 for both series. The arrows indicate the temperature T_{MAX} where the electrical resistivity has a maximum; (c) T_{MAX} as a function of the Cd concentration

two orders of magnitude larger than the residual resistivity of the $CeMIn_5$ (M = Co, Rh, Ir) compounds. This behavior is consistent with the typically larger chemical disorder of the 218 materials when compared to that of the 115 materials.^{33,34}

The most prominent feature of the resistivity data is the evolution of T_{MAX} , which, as shown in Fig. 4c, is increasing as a function of the Cd doping for both series. This behavior of T_{MAX} is not expected within the Doniach-like scenario used to interpret the behavior of T_N in these series.

From the point of view of the Doniach model, the decrease of a local density of states induced by Cd-doping drives the system to be more magnetic, i.e. the RKKY interactions are been favored while the Kondo effect is decreased. Based on this model, the T_{MAX} that is related to the Kondo energy scale should shift to lower temperatures as a function of the Cd concentration, in contrast to the observed results. This suggests that the Cd-doping may have a second effect that produces the

increase of the maximum in the resistivity. To further understand the role of Cd substitution in Ce_2MIn_8 we have performed X-ray and neutron magnetic scattering experiments to determine the low-T magnetic structure with Cd-doping.

B. Magnetic structure of Ce₂(Rh,Ir)In_{7.79}Cd_{0.21}

Cd-doping perturbations in the AFM state were further explored through X-ray and neutron magnetic scattering experiments. For these experiments we chose samples with the larger Néel temperature for both series with Cd concentration of x=0.21 and $T_N=4.8$ K and 3.8 K respectively to M = Rh and Ir.

The XRMS experiments were performed with the incident photon energy at the Ce-L₂ absorption edge in resonant condition in order to enhance the small signal from the AFM order of Ce^{3+} ions below T_N , and polarization analysis was performed to more properly determine the moment direction. Magnetic peaks of the Cd-doped Ce_2RhIn_8 with x = 0.21 were observed in dipolar resonant condition at temperatures below $T_N = 4.8 \text{ K}$ at reciprocal lattice points forbidden for charge scattering and consistent with an antiferromagnetic structure with propagation vector $(\frac{1}{2}, \frac{1}{2}, 0)^{35}$. This is the same propagation vector found by W. Bao et al.²³ for the pure compound, showing that Cd-doping is not changing the propagation vector. This indicates that although the Cddoping enhances the magnitude of the average magnetic exchange between neighboring Ce³⁺ ions it does not affect the sign of the relative magnetic interaction (and spin orientation) between them.

Figure 5a displays the temperature dependence of the magnetic moment of the Ce^{3+} ion, which is proportional to the square root of the integrated intensities, of the $(\frac{1}{2}, \frac{1}{2}, 9)$ magnetic reflection at an incident photon energy of 6164 eV (Ce-L₂ edge) and measured in σ - π ' polarization channel. A Voigt peak shape was used to fit transverse θ scans (sample rotation) through the reciprocal lattice points in order to obtain the integrated intensities. The data were taken between T = 2.0 K and T= 5.2 K while warming the sample. The inset shows the experimental θ -scans for two different temperatures, T=4.6 K (open triangles) and T = 2.0 K (closed squares), where one can observe the decrease of the intensity as T approaches T_N . The continuous line is a Voigt fit to the observed data at T = 2.0 K and show the very good quality of the crystal with a full width half maximum (FWHM) of 0.05° . The decrease of the intensities as the temperature is increased toward the bulk T_N demonstrates the magnetic character of this reflection, and is in very good agreement with the Néel temperature obtained from specific-heat measurements. The smooth decrease of the intensity through T_N is a signature of a secondorder-type transition.

Figure 5b shows the energy dependence of the $(\frac{1}{2}, \frac{1}{2}, 9)$ magnetic reflection around the Ce-L₂ absorption edge at

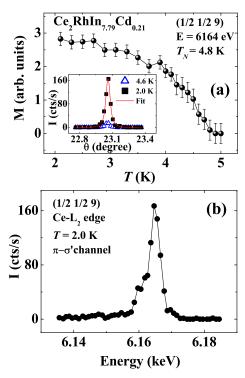


FIG. 5: (a) Temperature dependence of the ordered magnetic moment, proportional to square root of the integrated intensity, of the $(\frac{1}{2}, \frac{1}{2}, 9)$ magnetic reflection measured with transverse θ scans in the temperature range between T=2.0 and 5.2 K for Ce₂RhIn_{7.79}Cd_{0.21}. The inset shows two θ -scans of the same reflection for different temperatures: 4.6 K (open triangles) and 2.0 K (closed squares). The continuous line is a Voigt fit to the observed data at T=2.0 K. (b) Energy line shape of the $(\frac{1}{2},\frac{1}{2},9)$ magnetic peak at T=2.0 K for π - σ ' polarization channel at the Ce-L₂ absorption edge. The line is just a guide to the eye.

T=2.0 K. A resonant enhancement was observed at 1 eV above the absorption edges revealing a result consistent with a dominant electric dipolar character (E1) of this transition (from 2p to 5d states). These results confirm the magnetic origin of the $(\frac{1}{2},\frac{1}{2},l)$ reflections due to the existence of an antiferromagnetic structure doubled in the basal plane.

To completely determine the magnetic structure of the system an important aspect is the orientation of the magnetic ordered moment with respect to the crystal lattice. While the magnetic wave vector gives the relative orientation between the neighboring spins, the direction of moment gives information about the magnetic anisotropy (e.g. CEF effects) of the ordered spins. For collinear magnetic structures and polarized incident photons, the polarization dependence of the XRMS assumes a simple form for dipolar resonances, and the intensities of magnetic Bragg peaks are given by³⁶:

$$I \propto \frac{1}{\mu^* sin(2\theta)} \left| \sum_{n} f_{nE1}^{XRES}(\vec{k}, \hat{\epsilon}, \vec{k'}, \hat{\epsilon'}, \hat{z}_n) e^{i\vec{Q} \cdot \vec{R}_n} \right|^2, \quad (1)$$

where μ^* is the absorption correction for asymmetric

reflections, 2θ is the scattering angle, $\vec{Q} = \vec{k'} - \vec{k}$ is the wave-vector transfer, \vec{k} and $\vec{k'}$ ($\hat{\epsilon}$ and $\hat{\epsilon'}$) are the incident and scattered wave (polarization) vectors, respectively. \vec{R}_n is the position of the nth resonant atom in the lattice, $e^{i\vec{Q}\cdot\vec{R}_n}$ is the magnetic structure factor, and finally \hat{z}_n is the unit vector of the moment direction of the Ce³⁺ ions . The resonant scattering amplitude contains both dipole (E1) and quadrupole (E2) contributions. For the determination of the magnetic structure we have used the second term of the electric dipole transition (E1) form factor (f_{nE1}^{XRES}) which can be writen as:

$$f_{nE1}^{XRES} \propto \begin{bmatrix} 0 & \hat{k} \cdot \hat{z}_n \\ -\hat{k'} \cdot \hat{z}_n & (\hat{k} \times \hat{k'}) \cdot \hat{z}_n \end{bmatrix}$$
(2)

$$\propto \begin{bmatrix}
0 & z_1 cos\theta + z_3 sin\theta \\
-z_1 cos\theta + z_3 sin\theta & -z_2 sin(2\theta)
\end{bmatrix},$$
(3)

where θ is the Bragg angle, z_1 , z_2 and z_3 are the components of the magnetic moment at the nth site, according to the commonly used geometry convention of Ref. 37. In this convention each term of the matrix (Eq. 2) represents one polarization channel: σ , π , σ ' and π ' describe the incident (non-primed) and scattered (primed) photon polarizations. To describe the orientation of the magnetic moment, η is the angle of the moment with relation of the ab-plane and ψ the angle in the ab-plane.

magnetic structure of $Ce_2RhIn_{7.79}Cd_{0.21}$ was resolved by comparing the intensities of the $(\frac{1}{2}, \frac{1}{2}, l)$ (with l = 4, 5, 6, 7, 8, 9and 10) magnetic reflections with those expected using the model given in Eqs. $1 - 3^{29,36,38,39,40,41}$. For this determination we used the data obtained for $(\sigma - \pi')$ polarization channel measured with σ incident photons in the energy of the Ce-L₂ edge and T=2.0 K. For this channel the component of the matrix used was the term $-\hat{k}' \cdot \hat{z}_n$ of the Eq. 2. Since the tetragonal structure of Cd-doped Ce₂RhIn₈ contains two magnetic Ce³⁺ ions per unit cell in the c-direction, this implies that two possibilities of an AFM coupling can take place along the c-axis: 1) sequence + + or 2) sequence + -, where the symbols + and - represent the relative orientation of the magnetic moment of one Ce³⁺ ion with respect to the other. We checked the two sequences in our model and the sequence + - gives the better results, in agreement with the result obtained for pure Ce₂RhIn₈²³.

The experimental intensities of the magnetic peaks $(\frac{1}{2}, \frac{1}{2}, l)$ for Ce₂RhIn_{7.79}Cd_{0.21} are compared to the model discussed above and displayed in Figure 6. The best fit (solid line in Fig. 6) using the model was obtained for $\eta = 47^o \pm 3^o$ and $\psi = 45^o \pm 10^o$.

The results in Fig. 6 completely determine the magnetic structure of the $Ce_2RhIn_{7.79}Cd_{0.21}$ sample. The magnetic moment direction shows a slight evolution toward the basal plane when compared with the pure Ce_2RhIn_8 where the moment direction at 52^o to the

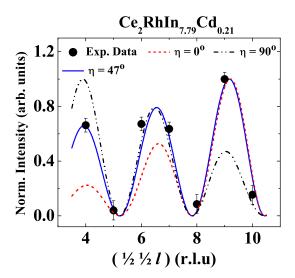


FIG. 6: The l dependence (in reciprocal lattice units) of the normalized intensities of the magnetic peaks $(\frac{1}{2}, \frac{1}{2}, l)$ measured at the energy of the Ce-L₂ edge at T=2.0 K in the σ - π ' polarization channel. The solid line represents the best fit using the model discussed in Eqs. 1- 3 for $\eta=47^o$ and $\psi=45^o$. The other lines represent the model calculated for $\psi=45^o$ and $\eta=0^o$ (dashed line) and $\eta=90^o$ (dashed-dot line)

basal plane. Those results indicate that Cd-doping also subtly changes the single ion anisotropy of the CEF GS which mainly determines the direction of the ordered moment. Analyzing these results in a more general way one can compare our results with those found for the In-based $R_m M_n In_{3m+2n}$ (M = Co, Rh or Ir; M = 1, 2; R = rare-earth) series. In a recent theoretical work using a mean field model including an isotropic first-neighbors (RKKY) interaction and the tetragonal CEF²⁸, it was demonstrated that, for realistic values of the interactions and CEF parameters, it is possible to determine qualitatively the direction of the ordered moments and the behavior of the ordering temperature for these series. Following the trend obtained for the In-based $R_m M_n In_{3m+2n}$ when the Néel temperature is higher the magnetic moment direction tends towards the c-axis, considering dominant CEF effects. Therefore, although the Cd-doping induces some changes in the CEF parameters, our results show that the direction of the ordered moment tend to rotate to the ab-plane even with an increase of the T_N for a Cd-doped sample, strongly suggesting that the dominant effect to raise T_N in these systems is the electronic tuning induced by the Cd-doping. The indication that the tetragonal CEF is changing as a function of Cd-doping in these series may explain the behavior of T_{MAX} in electrical resistivity measurements. If this subtle change in the CEF parameters leads to an increase of the energy level of the first excited doublet it may cause an increase in T_{MAX} . However, further experiments to obtain direct evidence of this change of CEF scheme as a function of Cd-doping is necessary to

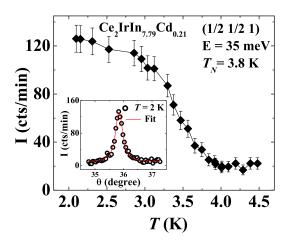


FIG. 7: Temperature dependence of the integrated intensities of the $(\frac{1}{2}, \frac{1}{2}, 1)$ magnetic reflection measured during heating the sample in the temperature range between T=2.0 K and T=4.5 K for Ce₂IrIn_{7.79}Cd_{0.21} for 35 meV. The inset shows the θ -scan of the same reflection for T=2.0 K where the continuous line is a Voigt fit to the observed data.

confirm this claim.

The NMS experiments were performed to study both Cd-doped Ce_2RhIn_8 and Ce_2IrIn_8 for x = 0.21 of Cd concentration. The Rh member was studied by NMS to determine the effective magnetic moment of the Ce³⁺ ions in low-T. The experiments were performed with an incident energy of 35 meV with no absorption corrections based on the fact that at 35 meV the neutron penetration length is about 2.0 mm, which is larger than the thickness of the sample. Indeed we measured rocking curves for different domains and no significant changes on the intensities were noticed. Magnetic peaks of the Ce₂(Rh,Ir)In_{7.79}Cd_{0.21} were observed at temperatures below $T_N = 4.8$ K and 3.8 K, respectively for Rh and Ir samples, at reciprocal lattice points forbidden for nuclear scattering and consistent with an antiferromagnetic structure with propagation vector $(\frac{1}{2}, \frac{1}{2}, 0)$. These results show that the Cd-doped Ce₂IrIn₈ sample presents the same propagation vector found for pure and Cd-doped Ce₂RhIn₈ samples.

Figure 7a displays the temperature dependence of the integrated intensity, of the $(\frac{1}{2},\frac{1}{2},1)$ magnetic reflection at an incident energy of 35 meV and measured between T=2.0 K and T=4.5 K while warming the sample. The inset shows an experimental θ -scan for T=2.0 K. The continuous line is a Voigt fit to the observed data at T=2.0 K and shows a FWHM of 0.2^o , a value larger than the one obtained for X-ray diffraction because of the larger divergence of the neutron beam compared with X-rays. The decrease of the intensity as the temperature is increased toward the bulk T_N indicates the magnetic char-

acter of this reflection, and are in very good agreement with the Néel temperature obtained from specific-heat measurements. The smooth decrease of the intensity is a signature of a second-order-type transition, found also for $\mathrm{Ce_2IrIn_{7.79}Cd_{0.21}}$ sample.

To completly determine the magnetic structure of $\text{Ce}_2\text{IrIn}_{7.79}\text{Cd}_{0.21}$ it is necessary to determine the magnetic moment orientation of the Ce^{3+} ion in relation to the crystallographic axis. Integrated intensities of magnetic Bragg peaks were determined using a Voigt fit in the θ -scans. These magnetic peaks were first normalized using the structural Bragg peaks (00l) for l=1,2,3,4, and 7; (11l) for l=1,2,3,4, 5, and 6 and (22l) for l=0,1,2,3, and 6. In barn units the magnetic cross section for a collinear magnetic structure using unpolarized neutrons is given by 23,42,43 :

$$\sigma(Q) = \left(\frac{\gamma r_0}{2}\right)^2 |M|^2 |f(Q)|^2 \sum_{\mu,\nu} (\delta_{\mu,\nu} - \hat{Q}_{\mu} \hat{Q}_{\nu}) F_{\mu}^*(Q) F_{\nu}(Q) (4)$$
FIG. 8: The l dependence (in reciprocal lattice units) of the

where $(\gamma r_0/2)^2 = 0.07265 \text{ b}/\mu_B^2$, M is the effective magnetic moment of the Ce³⁺ ion, f(Q) is the Ce³⁺ magnetic form factor⁴⁴, and $F_{\mu}(Q)$ is the $\mu^t h$ cartesian component of magnetic structure factor per Ce₂IrIn₈. The calculations were made considering the average of the possible domains and the result is given by²³:

$$\sigma(Q) = \left(\frac{\gamma r_0}{2}\right)^2 |M|^2 |f(Q)|^2 \left\langle 1 - (\hat{Q} \cdot \hat{z_n})^2 \right\rangle |F_M(Q)|^2 (5)$$

where $F_M(Q)$ is the magnetic form factor calculated for the two Ce^{3+} ions of the unitary cell along the c-axis, $\hat{z_n}$ is the unit vector of the magnetic moment, and the average, $\left\langle 1 - (\hat{Q} \cdot \hat{z_n})^2 \right\rangle$ is over the magnetic domains²³.

The NMS technique does not allow the moment direction determination in the ab-plane due to the square symmetry 42,43 , only the moment direction relative to the c-axis is allowed. Considering the magnetic moment with an arbitrary orientation in relation to the c-axis, there are in general 16 magnetic domains with tetragonal symmetry, for an equal population of domains, the average term of the Eq. 5 could be written as 23 :

$$\left\langle 1 - (\hat{Q} \cdot \hat{z_n})^2 \right\rangle = 1 - \frac{\cos^2 \alpha \, \cos^2 \eta + 2 \, \sin^2 \alpha \, \sin^2 \eta}{2}$$
 (6)

here α is the angle of \vec{Q} in relation to the basal plane and η is the angle between the moment direction and the basal plane.

Figure 8 shows the l dependence of the experimental $(\frac{1}{2}, \frac{1}{2}, l)$ magnetic intensities compared with the magnetic cross section $\sigma(Q)$ in mbarn units calculated using the model discussed in Eqs. 4 - 6. The solid line in Fig. 8 displays the best fit obtained for $\eta = 21^o \pm 5^o$ and the ordered magnetic moment at 2 K was determined as M = 0.4(5) μ_B per Ce. The model calculated for $\eta = 0^o$ is

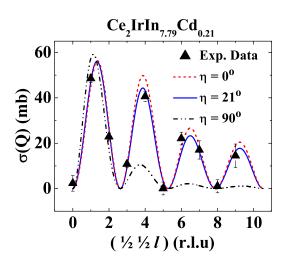


FIG. 8: The l dependence (in reciprocal lattice units) of the $\sigma(Q)$ of the magnetic peaks $(\frac{1}{2}, \frac{1}{2}, l)$ measured at the energy of 35 meV at T=2 K. The solid line represents the best fit using the model discussed in Eqs. 4 - 6 for $\eta=21^o$ and $M=0.22~\mu_B$. The other lines represent the model calculated for $\eta=0^o$ (dashed line) and $\eta=90^o$ (dashed-dot line).

represented by the dashed line while the dashed-dot line shows the model to $\eta = 90^{\circ}$.

The results in Fig. 8 completely determine the magnetic structure of $Ce_2IrIn_{7.79}Cd_{0.21}$ sample. The magnetic moment direction of the doped compound shows a large evolution toward to the basal plane when compared with the $Ce_2RhIn_{7.79}Cd_{0.21}$ where the moment direction lies at 47^o of the basal plane.

TABLE I: Magnetic Bragg intensities, σ_{obs} , (mbarn) observed at 1.6 K with E = 35 meV. The theoretical intensities, σ_{calc} (mbarn), were calculated using Eqs. 4 - 6 with $\eta = 47^{o}$ and M = 0.9(1) μ_{B} per Ce.

$ec{Q}$	σ_{exp}	σ_{calc}
$(\frac{1}{2}, \frac{1}{2}, 0)$	0.1(2)	0
$(\frac{1}{2}, \frac{1}{2}, 1)$	138(2)	134
$\left(\frac{1}{2}, \frac{1}{2}, 2\right)$	61(1)	56
$(\frac{1}{2}, \frac{1}{2}, 3)$	21(1)	19
$(\frac{1}{2}, \frac{1}{2}, 4)$	66(1)	69
$(\frac{1}{2}, \frac{1}{2}, 5)$	3(2)	4
$(\frac{1}{2}, \frac{1}{2}, 6)$	39(1)	30
$(\frac{1}{2}, \frac{1}{2}, 7)$	38(1)	28

NMS experiments were performed also in $Ce_2RhIn_{7.79}Cd_{0.21}$ to complement the study made with XRMS and to determine the effective magnetic moment M of this compound in low-T. Table I shows the observed magnetic integrated intensities of the $(\frac{1}{2}, \frac{1}{2}, l)$ (l = 0, 1, 2, 3, 4, 5, 6 and 7) magnetic reflections normalized by the nuclear peaks (00l) for l = 1, 2, 3,

4, and 7; (11*l*) for l=1, 2, 3, 4, 5, and 6 and (22*l*) for l=0, 1, 2, 3, and 6; the theoretical cross section was calculated using Eqs. 4 - 6 and the best fit the data is $\eta=47(5)^o$ and an ordered magnetic moment $M=0.9(2)~\mu_B$. The result of the magnetic moment direction found for Ce₂RhIn_{7.79}Cd_{0.21} sample is in very good agreement with the result found by means of the XRMS, showing the consistency of the two experimental methods. The novelty here is the ordered magnetic moment for Ce³⁺ ion in low-T equal to 0.9(2) μ_B that is a value larger than the value found for pure Ce₂RhIn₈, also consistently with the fact that Cd doping is favoring the AFM order in this system.

IV. CONCLUSIONS

The low temperature physical properties of Cd-doped Ce_2MIn_8 (M = Rh, Ir) single crystalline samples have been investigated. The results of the susceptibility, heat-capacity and resistivity as a function of temperature revealed an enhancement of the Néel temperature from 2.8 K for the pure compound to 4.8 K for the Cd-doped sample for M = Rh. For M = Ir an ordered AFM state at low Cd concentration and a subsequent evolution of the Néel temperature up to 3.8 K is found. This confirms the trend observed for the 115 compounds that the Cd-doping favors AFM ordering in these series and suggests that Cd is acting as an electronic tuning agent changing the local density of states that acts fundamentally

on the GS behavior. However there exist experimental evidences that Cd doping is affecting the tetragonal CEF parameters in these compounds. This is reflected in the tendency of the ordered moment to rotate to the ab-plane in Cd-doped samples. An evolution of the CEF scheme may also help to understand the behavior of T_{MAX} that increases as a function of Cd concentration. The increase of this parameter is not expected in a scenario where Cd is just acting as an electronic tuning agent. Further experiments like inelastic neutron scattering should be performed aiming to clarify the function of the Cd doping in the microscopic behavior on these systems. The XRMS and NMS experiments showed that Cd-doped Ce₂(Rh,Ir)In₈ has a commensurate magnetic order with propagation vector $\vec{\varepsilon} = (\frac{1}{2}, \frac{1}{2}, 0)$ identical to the pure Ce₂RhIn₈ compound, indicating that Cd-doping does not alter the sign of the relative magnetic interaction between the neighboring Ce spins, although it increases the magnitude of the average magnetic interaction between them as it can be seen by the increase of the ordered magnetic moment in the Cd-doped compounds.

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